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AMENDMENTS TO THE CLAIMS

Claims 113-119 are currently pending. Claims 1-112 are canceled.

1.-112. (Canceled)

113. (Original) A method of supporting a semiconductor wafer, comprising:

supporting a wafer on a susceptor;

permitting gas to flow through the susceptor between regions above and below the

susceptor;

supporting the susceptor on a plurality of support arms that extend generally

radially outward and upward from an upper section of a substantially vertical shaft, a

central vertical axis of the shaft being aligned with a central vertical axis of the susceptor,

the arms engaging the susceptor such that rotation of the shaft about the central vertical

axis of the shaft causes the susceptor to rotate about the central vertical axis of the

susceptor; and

rotating the shaft about the central vertical axis of the shaft.

114. (Original) The method of Claim 113, further comprising providing radiant energy

to the wafer and susceptor.

115. (Original) The method of Claim 113, wherein the support arms and the shaft are

transparent to radiant energy.

116. (Original) The method of Claim 113, wherein supporting the wafer on the

susceptor comprises supporting the wafer on a plurality of spacers extending upwardly

from an upper surface of the susceptor, such that the wafer is slightly spaced from the

upper surface.

117. (Original) The method of Claim 113, wherein permitting gas to flow through the

susceptor comprises permitting gas to flow through one or more gas flow passages in the

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susceptor, each of the one or more passages having an upper opening at an upper surface of the susceptor and a lower opening at a lower surface of the susceptor.

- 118. (Original) The method of Claim 117, wherein the one or more passages include horizontal channels inside the susceptor.
- 119. (Original) The method of Claim 113, wherein supporting the susceptor comprises inserting upper ends of the support arms into cavities within a lower surface of the susceptor, each of the cavities positioned along a circle centered on the central vertical axis of the shaft.